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MARCH 1997 - REVISED SEPTEMBER 1997

#### TELECOMMUNICATION SYSTEM SECONDARY PROTECTION

 Ion-Implanted Breakdown Region Precise and Stable Voltage Low Voltage Overshoot under Surge

DEVICE	V <sub>(Z)</sub>	V <sub>(BO)</sub>
DEVICE	٧	٧
'4240LP	180	240

- Planar Passivated Junctions Low Off-State Current < 10 μA</li>
- Rated for International Surge Wave Shapes

	WAVE SHAPE	STANDARD	I <sub>TSP</sub>
I	10/700 µs	CCITT IX K17	38

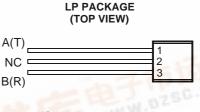
## Package Options

PACKAGE	PACKING	PART # SUFFIX
LP	Bulk	None
LP with fomed leads	Tape and Reel	R

## description

The TISP4240LP is designed specifically for telephone equipment protection against lightning and transients induced by a.c. power lines. These devices consist of a bidirectional suppressor element connecting the A and B terminals. They will suppress inter-wire voltage transients.

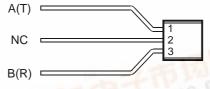
Transients are initially clipped by zener action until the voltage rises to the breakover level, which causes the device to crowbar. The high crowbar holding current prevents d.c. latchup as the transient subsides.



NC - No internal connection

**MDTRAB** 

LP PACKAGE WITH FORMED LEADS (TOP VIEW)



NC - No internal connection

MD4XAI

# device symbol



These monolithic protection devices are fabricated in ion-implanted planar structures to ensure precise and matched breakover control and are virtually transparent to the system in normal operation.



# TISP4240LP SYMMETRICAL TRANSIENT VOLTAGE SUPPRESSORS

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## absolute maximum ratings at 25°C case temperature (unless otherwise noted))

RATING	SYMBOL	VALUE	UNIT
Non-repetitive peak on-state pulse current (see Notes 1, 2 and 3)	1		۸
5/310 μs (CCITT IX K17, open-circuit voltage wave shape 1.5 kV, 10/700 μs)	ITSP	38	A
Non-repetitive peak on-state current, 50 Hz, 1 s (see Notes 1 and 2)	I <sub>TSM</sub>	2.5	A rms
Initial rate of rise of on-state current, Linear current ramp, Maximum ramp value < 38 A	di <sub>T</sub> /dt	250	A/µs
Junction temperature	$T_J$	150	°C
Operating free - air temperature range		0 to 70	°C
Storage temperature range	T <sub>stg</sub>	-40 to +150	°C
Lead temperature 1.5 mm from case for 10 s	T <sub>lead</sub>	260	°C

- NOTES: 1. Above 70°C, derate linearly to zero at 150°C case temperature
  - 2. This value applies when the initial case temperature is at (or below) 70°C. The surge may be repeated after the device has returned to thermal equilibrium.
  - 3. Most PTT's quote an unloaded voltage waveform. In operation the TISP essentially shorts the generator output. The resulting loaded current waveform is specified.

# electrical characteristics, $T_J = 25$ °C

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>Z</sub>	Reference zener	$I_7 = \pm 1 \text{mA}$	± 180			V
٧Z	voltage	1Z - ± 11110	± 100			v
∝VZ	Temperature coefficient			0.1		%/°C
	of reference voltage			0.1		767 C
V <sub>(BO)</sub>	Breakover voltage	(see Notes 4 and 5)			± 240	V
I <sub>(BO)</sub>	Breakover current	(see Note 4)	± 0.15		± 0.6	Α
$V_{TM}$	Peak on-state voltage	$I_T = \pm 5 \text{ A}$ (see Notes 4 and 5)		± 2.2	± 3	V
I <sub>H</sub>	Holding current	(see Note 4)	± 150			mA
dv/dt	Critical rate of rise of	(see Note 6)			± 5	kV/μs
dv/di	off-state voltage					
I <sub>D</sub>	Off-state leakage	$V_D = \pm 50 \text{ V}$			± 10	μΑ
	current	vD - ± 00 v			± 10	μΛ
C <sub>off</sub>	Off-state capacitance	$V_D = 0$ $f = 1 \text{ kHz}$		70	150	pF

- NOTES: 4. These parameters must be measured using pulse techniques,  $t_w = 100 \mu s$ , duty cycle  $\leq 2\%$ .
  - 5. These parameters are measured with voltage sensing contacts seperate from the current carrying contacts located within 3.2 mm (0.125 inch) from the device body.
  - 6. Linear rate of rise, maximum voltage limited to 80 %  $\rm V_{\rm Z}$  (minimum).

### thermal characteristics

	PARAMETER		TYP	MAX	UNIT
$R_{\theta JA}$	Junction to free air thermal resistance			156	°C/W

# PARAMETER MEASUREMENT INFORMATION

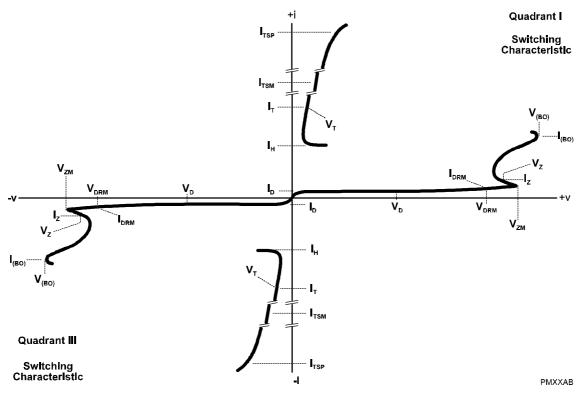


Figure 1. VOLTAGE-CURRENT CHARACTERISTICS FOR TERMINALS A AND B

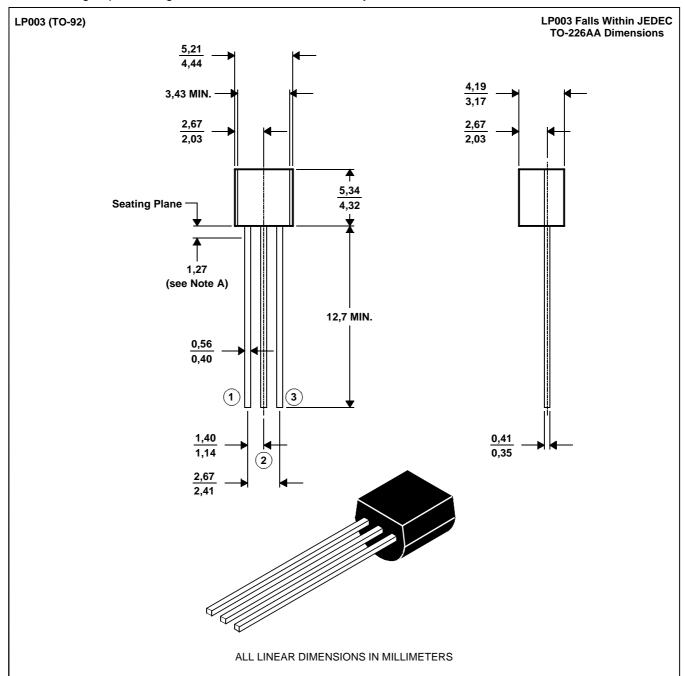
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### **MECHANICAL DATA**

# LP003 (TO-92)

# 3-pin cylindical plastic package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTE A: Lead dimensions are not controlled in this area.

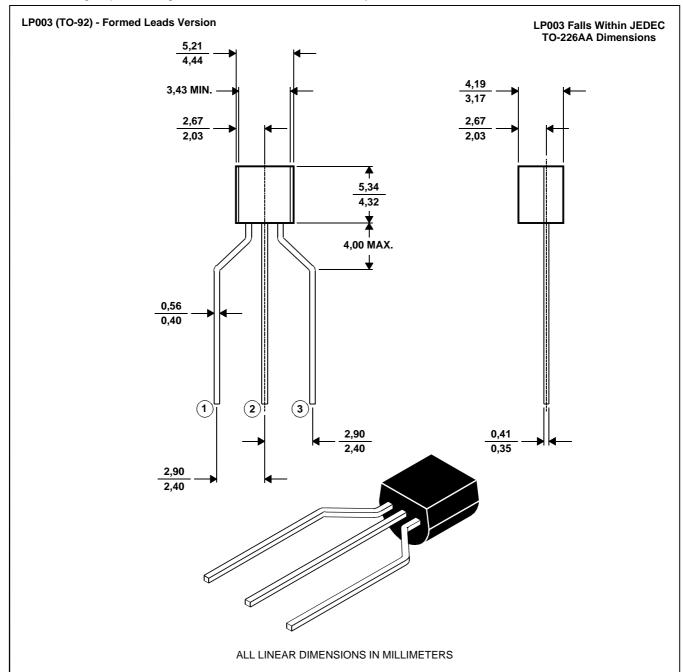
MDXXAX

#### **MECHANICAL DATA**

## LP003 (TO-92)

## 3-pin cylindical plastic package

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MDXXAR

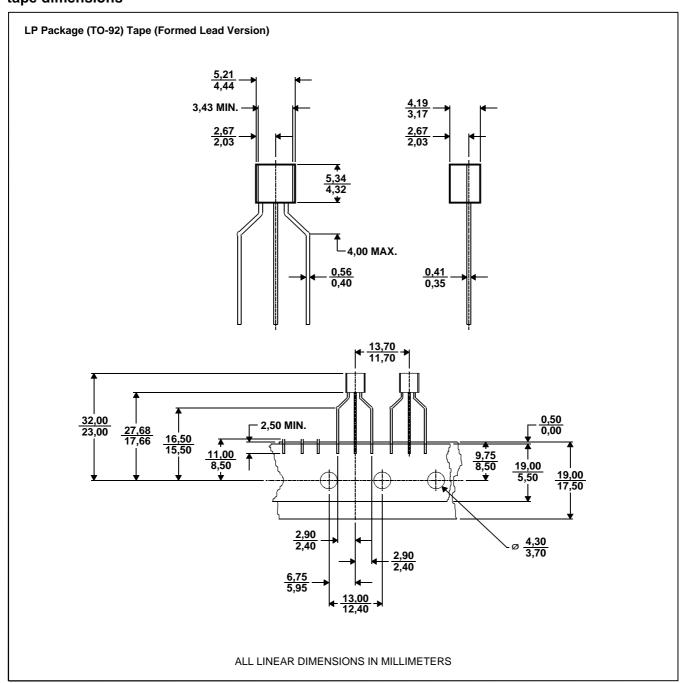


# TISP4240LP SYMMETRICAL TRANSIENT VOLTAGE SUPPRESSORS

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## **MECHANICAL DATA**

# LPR tape dimensions



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